



MJ10016

NPN Silicon Darlington High Power Transistor



Features:

1. Using triple-diffusion process.High output current. Small driving power.
2. Highest amplification factor. High inverse voltage.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for current output,voltage adjustment and servo circuit of numerical control machine.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Collector-Emitter Voltage	V_{CEO}	V	600	
Emitter-Base Voltage	V_{EBO}	V	8	
Max. Collector Current	I_{CM}	A	50	
Max. Collector Dissipation	P_{CM}	W	250	$T_c:75^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	175	
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175	
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0	$V_{CE}=600\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.2	$I_c=20\text{A}, I_B=1\text{A}$
DC Current Gain	h_{FE}		Min.:25	$V_{CE}=5\text{V}, I_c=20\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	600	$I_c=1\text{mA}$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5	$I_E=20\text{mA}$

Outline and Dimensions: